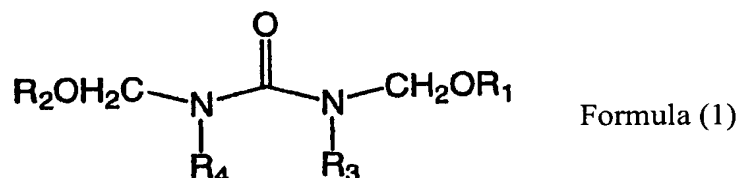


Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An anti-reflective coating forming composition, used for lithography process for manufacturing a semiconductor device comprising a compound of formula (1), a condensation product thereof or a resin produced from the compound



wherein R₁ and R₂ are independently of each other hydrogen atom or an alkyl group, R₃ and R₄ are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxymethyl group, and an acid and/or acid generator, and the compound, the condensation product thereof or the resin produced from the compound is contained in an amount of 50 mass% or more in a solid content of the anti-reflective coating forming ~~composition.~~ composition.

wherein the anti-reflective coating forming composition is an underlayer of a resist and subjected to dry etching.

2-3. (Canceled)

4. (Previously Presented) The anti-reflective coating forming composition according to claim 1, further containing a light absorbing compound and/or a light absorbing resin.

5. (Previously Presented) The anti-reflective coating forming composition according to claim 4, wherein the light absorbing compound is at least one compound selected from naphthalene compounds and anthracene compounds.

6. (Previously Presented) The anti-reflective coating forming composition according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.

7. (Previously Presented) The anti-reflective coating forming composition according to claim 4, wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.

8. (Previously Presented) The anti-reflective coating forming composition according to claim 1, further containing a resin having at least one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.

9. (Canceled)

10. (Previously Presented) A method of forming an anti-reflective coating for use in lithography process in a manufacture of a semiconductor device, characterized by comprising the steps of: coating anti-reflective coating forming composition according to claim 1 on a substrate, and baking it.

11. (Previously Presented) A process for manufacturing a semiconductor device, characterized by comprising the steps of:

coating anti-reflective coating forming composition according to claim 1 on a substrate and baking it to form an anti-reflective coating;

forming a photoresist on the anti-reflective coating;

exposing the substrate covered with the anti-reflective coating and the photoresist with a light;

developing it;

transferring an image on the substrate by etching to form an integrated circuit device.